

1. 单选题 (2.0分)

In a P-type semiconductor material, the majority carriers are _____.

- ☐ A.free electrons
- ☐ B.holes
- ☐ C.impurity irons
- ☐ D.valence elections

2. 单选题 (2.0分)

In a semiconductor diode, the region near the PN junction consisting of positive and negative ions is called the _____.

- ☐ A.neutral zone
- ☐ B.recombination region
- ☐ C.depletion region
- ☐ D.diffusion area

3. 单选题 (2.0分)

To form the positive material in the semiconductor, which element can be doped? _____.

- ☐ A.group IV elements
- ☐ B.group V elements
- ☐ C.group III elements
- ☐ D.group VI elements

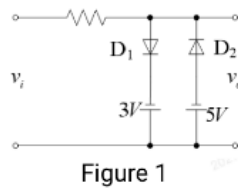
4. 单选题 (2.0分)

For a Zener diode, in the Zener region the current _____ and the voltage across the diode _____.

- ☐ A.is almost constant; is almost constant
- ☐ B.can increase a lot; is almost constant
- ☐ C.is almost constant; can increase a lot
- ☐ D.can increase a lot; can increase a lot

5. 单选题 (2.0分)

For circuit shown in **Figure 1**, the diode is ideal; if the input DC voltage $v_i > 0$, the output is _____.



- ☐ A. -8V
- ☐ B. -2V
- ☐ C. -5V
- ☐ D. -3V

6. 单选题 (2.0分)

For an PNP transistor working in active region, the DC voltages at three pins are -2V, -2.7V and -6V. The pins are _____ terminal.

- ☐ A. Base, Collector, Emitter
- ☐ B. Base, Emitter, Collector
- ☐ C. Collector, Base, Emitter
- ☐ D. Emitter, Base, Collector

7. 单选题 (2.0分)

To be employed as linear (undistorted) amplifiers for NPN transistor, the B-E junction of BJTs should be _____ biased and the B-C junction of BJTs should be _____ biased.

- ☐ A. forward, forward
- ☐ B. forward, reverse
- ☐ C. reverse, reverse
- ☐ D. reverse, forward

8. 单选题 (2.0分)

Which of the following is not true for the BJT circuit in **Figure 2** ____? (Assuming the knee voltage of B-E junction is 0.7V)

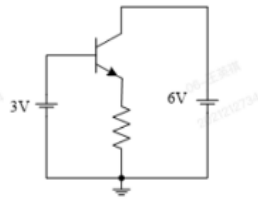


Figure 2

- ☐ A. The base voltage is 3V.
- ☐ B. The voltage between collector and emitter is 3.7V.
- ☐ C. The emitter voltage is 0.7V.
- ☐ D. The collector voltage is 6V.

9. 单选题 (2.0分)

In a common emitter amplifier, the output voltage is always _____ with the input voltage in full frequency band.

- ☐ A. 45° out of phase
- ☐ B. 90° out of phase
- ☐ C. 180° out of phase
- ☐ D. None of above

10. 单选题 (2.0分)

For an emitter follower, the input impedance is relatively _____ and the output impedance quite _____.

- ☐ A. high, small
- ☐ B. small, high
- ☐ C. small, small
- ☐ D. high, high

11. 单选题 (2.0分)

For the transistor amplifier circuit, if the quiescent point is low, then _____ happens, if the quiescent point is high, then _____ happens.

- ☐ A. Saturation distortion, Cut-off distortion
- ☐ B. Cut-off distortion, Saturation distortion
- ☐ C. Saturation distortion, Saturation distortion
- ☐ D. Cut-off distortion, Cut-off distortion

12. 单选题 (2.0分)

The region of the characteristic curve family for the FETs that is normally used for linear amplification is _____.

- ☐ A. the linear-resistance region
- ☐ B. the Ohmic region
- ☐ C. the saturation region
- ☐ D. All of the above

13. 单选题 (2.0分)

The minimum current in a JFET occurs when V_{GS} is equal to _____.

- ☐ A. pinch-off voltage
- ☐ B. zero Voltage
- ☐ C. a voltage greater than the pinch-off voltage
- ☐ D. a small positive voltage

14. 单选题 (2.0分)

A _____ is a voltage-controlled device and a _____ is a current-controlled device.

- ☐ A. BJT, FET
- ☐ B. BJT, FFT
- ☐ C. FET, BJT
- ☐ D. BCE, FJT

15. 单选题 (2.0分)

For the voltage divider circuit, the NPN BJT common emitter configuration, the voltage gain is__.

- ☐ A. $A_u = -(R_C || r_o) / r_e$
- ☐ B. $A_u = -(R_1 || r_o) / r_e$
- ☐ C. $A_u = -(R_2 || r_o) / r_e$
- ☐ D. None of above

16. 单选题 (2.0分)

Calculate the JFET amplifier with load in **Figure 3**. Assume that $g_m = 2\text{mS}$, $R_D = 4\text{k}\Omega$, $R_L = 4\text{k}\Omega$ _____.

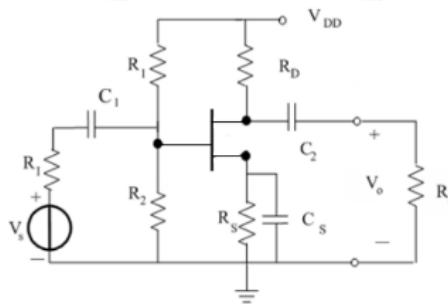


Figure 3

- ☐ A. $A_u = 4$
- ☐ B. $A_u = 1$
- ☐ C. $A_u = -4$
- ☐ D. $A_u = -1$

17. 单选题 (2.0分)

For the common emitter amplifier, ___ capacitors do not affect the low frequency response.

- ☐ A. bypass
- ☐ B. input coupling
- ☐ C. output coupling
- ☐ D. interelectrode

18. 单选题 (2.0分)

For BJT amplifiers, the high frequency and low-frequency gain is _____.

- ☐ A.decreased
- ☐ B.increased
- ☐ C.constant
- ☐ D.None of above

19. 单选题 (2.0分)

When a BJT transistor is used in a switching circuit, it operates in the _____.

- ☐ A.saturation and active regions
- ☐ B.active and cutoff regions
- ☐ C.saturation and cutoff regions
- ☐ D.active region only

20. 单选题 (2.0分)

If a resistor is added in the emitter for the CE amplifier, which is not bypassed by a capacitor, then the voltage gain of the small signal CE amplifier will _____.

- ☐ A.decrease
- ☐ B.increase
- ☐ C.increase in some cases and decrease in other cases
- ☐ D.stay the same

21. 单选题 (2.0分)

When comparing the common emitter and the common collector amplifiers, the input impedance of the common _____ is much larger and the output impedance of the common _____ is much smaller.

- ☐ A.emitter; emitter
- ☐ B.emitter; collector
- ☐ C.collector; emitter
- ☐ D.collector; collector

22. 单选题 (2.0分)

The common-base amplifier is characterized as having a relatively _____ input impedance and relatively _____ output impedance.

- ☐ A. high; low
- ☐ B. low; low
- ☐ C. low; high
- ☐ D. high; high

23. 单选题 (2.0分)

For an unload BJT amplifier, voltage gain is -100, output impedance is 20, terminal load is 80, the loaded voltage gain is _____.

- ☐ A. -20
- ☐ B. +20
- ☐ C. +80
- ☐ D. -80

24. 单选题 (2.0分)

Crossover distortion in class B power amplifiers can be prevented by _____.

- ☐ A. biasing the transistors slightly above cutoff.
- ☐ B. biasing the transistors deeply into cutoff.
- ☐ C. using complementary-symmetry transistors.
- ☐ D. increasing the load resistance.

25. 单选题 (2.0分)

Ideally, the _____ amplifier has larger gain for the differential mode signal, and has no gain for the common mode signal.

- ☐ A. transistor
- ☐ B. power
- ☐ C. common
- ☐ D. differential

26. 简答题 (10.0分)

For the network shown in **Figure 4**, $V_T=26\text{mV}$ (at room temperature):

- 1) Describe how to get the DC equivalent circuit. **(1 marks)**
- 2) Assume $V_{BE(on)}=0.7\text{V}$, determine the Q point: V_B, I_E, r_e . **(3 marks)**
- 3) Describe how to get the AC equivalent circuit. **(2 marks)**
- 4) Find the A_u, Z_i and Z_o with $r_o = \infty \text{ Ohm}$. **(3 marks)**
- 5) If the load $R_L=3.9\text{k}\Omega$ is added to the output, calculate the voltage gain A_u . **(1 marks)**

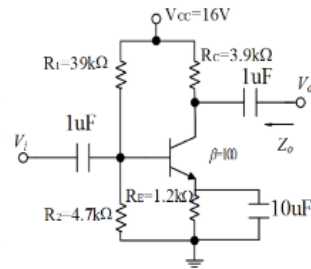


Figure 4

27. 简答题 (12.0分)

A differential amplifier is shown in **Figure 5**. For the transistors T_1 and T_2 , $\beta=100$, $r_{ce}=\infty$, $U_{BE(on)}=0.6V$, $V_T=26mV$ (at room temperature).

- 1) Calculate static collector current I_{CQ1} and I_{CQ2} . (2 marks)
- 2) Calculate static voltage V_{C1} and V_{C2} . (1 marks)
- 3) Calculate the r_e parameter of the ac equivalent model. (2 marks)
- 4) For a double output, calculate the differential mode voltage gain. (2 marks)
- 5) For a double output, calculate the differential mode input resistance. (2 marks)
- 6) For a double output, calculate the differential mode output resistance. (1 marks)
- 7) For a double output, calculate the common mode voltage gain. (1 marks)
- 8) For a double output, calculate the CMRR. (1 marks)

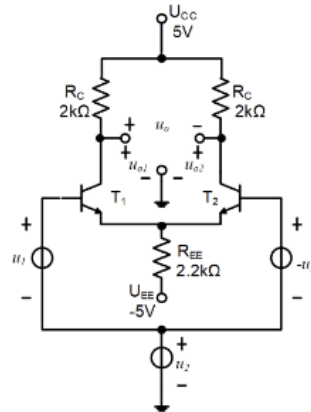


Figure 5

28. 简答题 (5.0分)

For the negative feedback circuit in **Figure 6**, answer the questions.

- 1) Determine the type of the negative feedback. **(1 marks)**
- 2) If the AC negative feedback is strong enough, calculate the voltage gain by approximate analysis method. **(2 marks)**
- 3) If the AC negative feedback is strong enough, calculate the input impedance and output impedance. **(2 marks)**

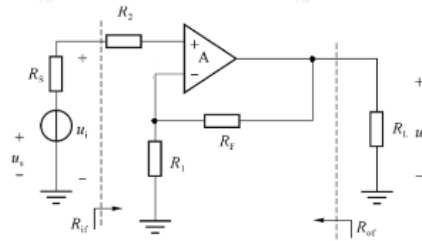


Figure 6

29. 简答题 (5.0分)

For the negative feedback circuit in **Figure 7**, answer the questions.

- 1) Determine the type of the negative feedback. **(1 marks)**
- 2) If the AC negative feedback is strong enough, calculate the voltage gain by approximate analysis method. **(2 marks)**
- 3) If the AC negative feedback is strong enough, calculate the input impedance and output impedance. **(2 marks)**

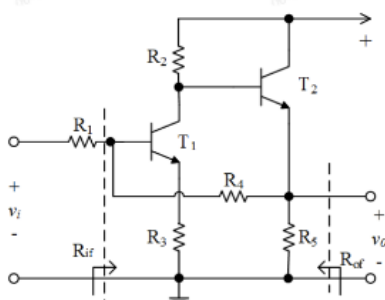


Figure 7

30. 简答题 (8.0分)

For complementary symmetric power amplifier circuit shown in **Figure 8**, the base bias circuit is omitted. VT_2 and VT_3 are output transistors. Assume that the saturation voltages of VT_2 and VT_3 are negligible. The voltage on R_4 and R_5 are negligible.

- 1) Determine the static voltage of point A. (1 marks)
- 2) What are the role of the connection of D_1 and D_2 ? (1 marks)
- 3) Find the maximum AC output power. (2 marks)
- 4) Find the maximum input power from the DC supply. (2 marks)
- 5) Find the maximum power efficiency. (1 marks)
- 6) Find the power dissipation by both T_2 and T_3 when the output power is maximum. (1 marks)

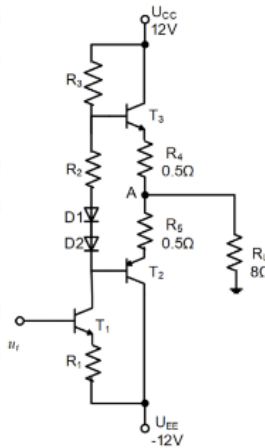


Figure 8

31. 简答题 (10.0分)

In the circuit of **Figure 9**, the op-amp are ideal. Zener Diode with $V_Z = \pm 10V$, $R_1 = 100K\Omega$, $R_2 = 2K\Omega$, $R = 10K\Omega$, $C = 1\mu F$, $v_{i1} = -5V$, $v_{i2} = 5.1V$, $V_R = -7V$, Power supply $V_{CC} = \pm 15V$, at $t=0$, $v_C = 0V$. If connected to power supply at $t=0$, determine the function of each stage, and calculate the voltage output of each stage at $t=5.1s$. (note: calculate v_{o1} , v_{o2} , v_{o3} , v_{o4} , v_{o5} , v_{o6} , v_o)

